High Current Transistors

PNP Silicon

• Device Marking: 490

490A 490B

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	-80	Vdc
Collector-Base Voltage	VCBO	-80	Vdc
Emitter-Base Voltage	V _{EBO}	-4.0	Vdc
Collector Current — Continuous	IC	-1.0	Adc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	–55 to +150	°C

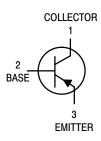
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	R _θ JC	83.3	°C/W



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CASE 29 TO-92 STYLE 17

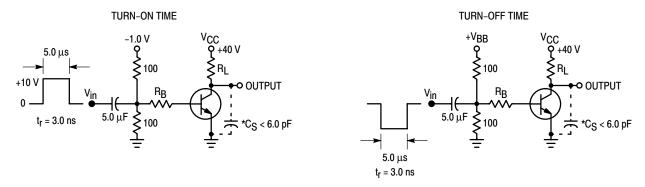
ORDERING INFORMATION

Device	Package	Shipping
BC490	TO-92	5000 Units/Box
BC490A	TO-92	5000 Units/Box
BC490AZL1	TO-92	2000/Ammo Pack
BC490BZL1	TO-92	2000/Ammo Pack

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

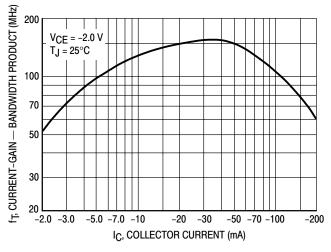
Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage ⁽¹⁾ (I _C = -10 mAdc, I _B = 0)	V(BR)CEO	-80	_	_	Vdc	
Collector–Base Breakdown Voltage (I _C = –100 μAdc, I _E = 0)	V(BR)CBO	-80	_	_	Vdc	
Emitter–Base Breakdown Voltage ($I_E = -10 \mu Adc$, $I_C = 0$)	V(BR)EBO	-4.0	_	_	Vdc	
Collector Cutoff Current (V _{CB} = -60 Vdc, I _E = 0)	ICBO	_	_	-100	nAdc	
ON CHARACTERISTICS*	ON CHARACTERISTICS*					
DC Current Gain	hFE	40 60 100 160 15	 140 		_	
Collector–Emitter Saturation Voltage (I _C = -500 mAdc, I _B = -50 mAdc) (I _C = -1.0 Adc, I _B = -100 mAdc)	VCE(sat)	_	-0.25 -0.5	-0.5 	Vdc	
Base–Emitter Saturation Voltage (I _C = -500 mAdc, I _B = -50 mAdc) (I _C = -1.0 Adc, I _B = -100 mAdc)	V _{BE} (sat)	_	-0.9 -1.0	-1.2 	Vdc	
DYNAMIC CHARACTERISTICS						
Current–Gain — Bandwidth Product (I _C = -50 mAdc, V _{CE} = -2.0 Vdc, f = 100 MHz)	fΤ	_	150	_	MHz	
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{ob}	_	9.0	_	pF	
Input Capacitance (VEB = -0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{ib}	_	110	_	pF	

^{1.} Pulse Test: Pulse Width = 300 μs, Duty Cycle 2%.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits



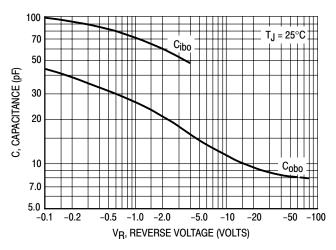


Figure 2. Current-Gain — Bandwidth Product

Figure 3. Capacitance

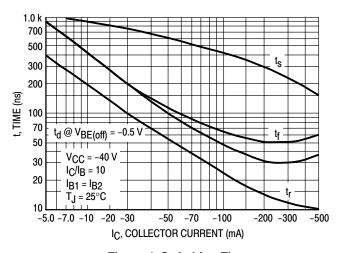


Figure 4. Switching Time

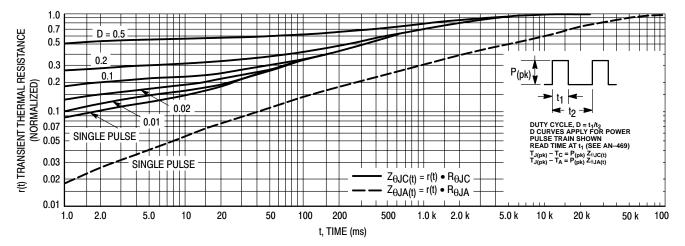


Figure 5. Thermal Response

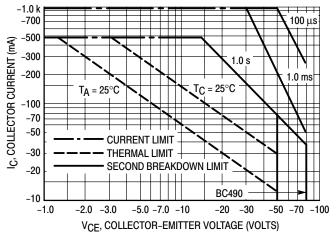


Figure 6. Active Region, Safe Operating Area

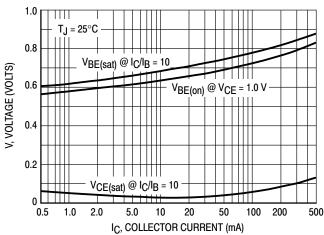


Figure 7. "On" Voltages

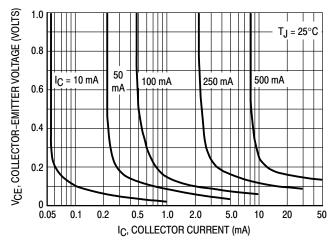


Figure 8. Collector Saturation Region

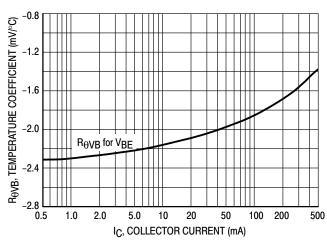


Figure 9. Base-Emitter Temperature Coefficient

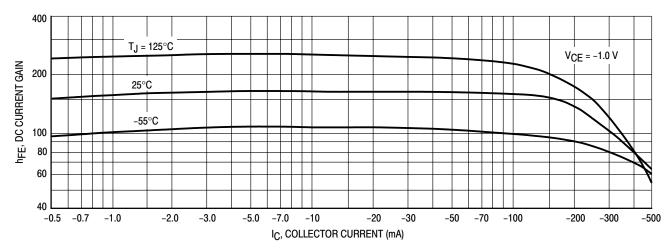
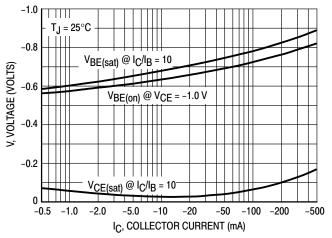


Figure 10. DC Current Gain



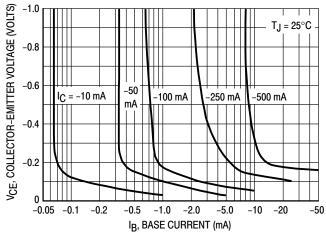


Figure 11. "On" Voltages

Figure 12. Collector Saturation Region

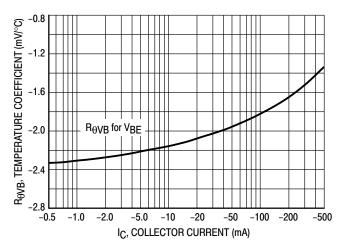
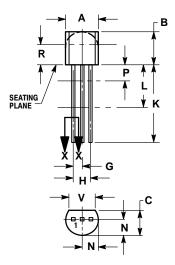


Figure 13. Base-Emitter Temperature Coefficient

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

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